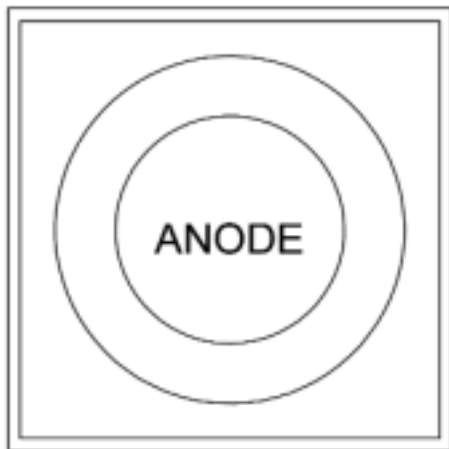


PROCESS DETAILS

| | |
|------------------------|-------------------|
| Process | EPITAXIAL PLANAR |
| Die Size | 17.5 x 17.5 MILS |
| Die Thickness | 8.0 MILS |
| Anode Bonding Pad Area | 8.0 MILS DIAMETER |
| Top Side Metalization | Al - 15,000Å |
| Back Side Metalization | Au - 6,000Å |

GEOMETRY



BACKSIDE CATHODE

PRINCIPAL DEVICE TYPES

CMPD2003
CMPD2004
1N3070

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